

Lso Johansson

List of Publications by Year in descending order

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papers

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citations

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30
all docs

30
docs citations

30
times ranked

284
citing authors

#	ARTICLE	IF	CITATIONS
1	Spin coupling in Ag film growth on Sn/Ge(111)-3Å-3. Surface Science, 2022, 719, 122043.	1.9	0
2	Initial quantum well states in Ag thin films on the In/Si(111)-3Å-3 surface. Surface Science, 2020, 692, 121531.	1.9	5
3	Layer-by-layer control of Ag film growth on Sn/Si(111)-(3Å-3)-R30°. Surface Science, 2020, 701, 121697.	1.9	4
4	Photoelectron spectroscopy studies of PTCDA on Sn/Si(111)-23Å-23. Chemical Physics, 2020, 539, 110973.	1.9	3
5	STM/STS and photoemission study of Ag thin films on Ga/Si(111) ($\sqrt{3} \times \sqrt{3}$). Surface Science, 2019, 682, 25-32.	1.9	8
6	Electronic structure of PTCDA on Sn/Si(1 1 1)- $\sqrt{3} \times \sqrt{3}$. Chemical Physics, 2014, 439, 71-78.	1.9	6
7	STM study of the electronic structure of PTCDA on Ag/Si(1 1 1)- $\sqrt{3} \times \sqrt{3}$. Chemical Physics Letters, 2010, 485, 69-76.	2.6	20
8	Two-dimensional states in the electronic structure of Au/ -4H-SiC(0001). Journal of Electron Spectroscopy and Related Phenomena, 2008, 163, 1-6.	1.7	0
9	Surface resonance on the -reconstructed 5ML Au on -4H-SiC(0001). Surface Science, 2007, 601, 2508-2511.	1.9	1
10	Investigation of surface structure related features in the multiple-scattering simulations of photoelectron diffraction of 3C-SiC(001)-. Physica B: Condensed Matter, 2007, 395, 130-137.	2.7	4
11	Growth and characterization of thin PTCDA films on 3C-SiC(001)- $\sqrt{2} \times \sqrt{2}$. Surface Science, 2006, 600, 4758-4764.	1.9	8
12	Core-Level Photoemission From Stoichiometric GaN(0001)- $\sqrt{3} \times \sqrt{3}$. MRS Internet Journal of Nitride Semiconductor Research, 2005, 10, 1.	1.0	12
13	Angle-resolved photoemission from stoichiometric GaN(0001)- $\sqrt{3} \times \sqrt{3}$. Surface Science, 2005, 584, 169-178.	1.9	18
14	Preparation of stoichiometric GaN(0001)- $\sqrt{3} \times \sqrt{3}$: an XPS study. MRS Internet Journal of Nitride Semiconductor Research, 2004, 9, 1.	1.0	8
15	Thin PTCDA films on Si(001): 2. Electronic structure. Surface Science, 2004, 572, 32-42.	1.9	28
16	Thin PTCDA films on Si(001): 1. Growth mode. Surface Science, 2004, 572, 23-31.	1.9	31
17	Preparation of stoichiometric GaN(0001)- $\sqrt{3} \times \sqrt{3}$ studied with spectromicroscopy. Surface Science, 2004, 572, 409-417.	1.9	7
18	Study of Si2p core level shift at the As/Si(001)- $\sqrt{2} \times \sqrt{2}$ surface. Surface Science, 2002, 499, 244-250.	1.9	2

#	ARTICLE	IF	CITATIONS
19	Imaging of the electronic states on the Si(1 1 1)1Å–1As surface using a display-type photoelectron analyzer. Surface Science, 2001, 482-485, 600-605.	1.9	0
20	Angle-resolved photoemission study of the hydrogenated 3C-SiC(001)-2Å–1-H surface. Surface Science, 2001, 479, 247-254.	1.9	13
21	Electronic structure of the 6HAsSiC(0001)-3Å–3 surface studied with angle-resolved inverse and direct photoemission. Surface Science, 2000, 445, 109-114.	1.9	40
22	Electronic structure of the 3CAsSiC(001)2Å–1 surface studied with angle-resolved photoelectron spectroscopy. Surface Science, 1999, 439, 199-210.	1.9	8
23	Adsorption of Rb on Si(100)2 Å– 1 at room temperature studied with photoelectron spectroscopy. Applied Surface Science, 1998, 123-124, 76-81.	6.1	7
24	Core-level study of the system: beyond the room temperature saturation coverage. Surface Science, 1997, 372, 64-70.	1.9	11
25	Photoemission study of Na growth on the Si(100)c(4 Å– 2) surface at low temperature. Surface Science, 1997, 391, 237-244.	1.9	6
26	Angle dependence of the spin-orbit branching ratio. Surface Science, 1996, 352-354, 352-357.	1.9	14
27	Photoemission study of low coverage potassium adsorption on the Si(111)1 Å– 1:As surface. Surface Science, 1995, 342, 293-298.	1.9	5
28	Surface electronic structure of clean and hydrogen chemisorbed Ge(100)2 Å– 1 studied by angle-resolved photoemission. Vacuum, 1990, 41, 635-637.	3.5	9
29	Electronic structure of the hydrogen chemisorbed Si(100)2Å–1-H surface: An angle resolved photoemission study. Surface Science, 1987, 189-190, 479-484.	1.9	41
30	Electronic structure of the hydrogen chemisorbed Si(100)2x1-H surface: An angle resolved photoemission study. Surface Science Letters, 1987, 189-190, A419.	0.1	1